

whereby the forming by atomic layer deposition one or more layers of a monocrystalline high dielectric constant oxide includes exposing the monocrystalline seed layer to a metal precursor, thereby forming a layer of metal, flushing the layer of metal with an inert gas, exposing the layer of metal to at least one of oxygen (O) with or without plasma, water (H₂O), nitrous oxide (N₂O), or nitric oxide (NO) to oxidize the layer of metal thereby forming a single monocrystalline high-k oxidized monolayer, and flushing the oxidized monolayer with an inert gas.

31. A method of fabricating a semiconductor structure as claimed in claim 30 further including repeating the atomic layer deposition to form monocrystalline high-k oxide of a desired thickness.--

REMARKS

New claims 21-31 replace claims 3, 5-8, and 13-18.

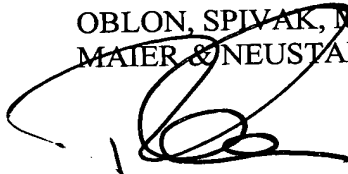
The rejection of claims 3, 5-8, and 13-18 as obvious over Yu is traversed.

The present application was filed on June 21, 2001. Accordingly, the provisions of 35 U.S.C. 103(c) apply. Yu thus is not prior art against the present application because Yu and the present application were, at the time the invention was made, owned by, or subject to an obligation of assignment to, the same corporate person. See MPEP 706.02(l)(3) regarding 35 U.S.C. 103(c) and 706.02(l)(2) regarding the above statement of common assignment. As Yu is not prior art against the present application, the rejection based on this reference is unsustainable, and should be withdrawn.

Accordingly, Applicants submit that this application is now in condition for allowance, and early notification thereof is respectfully requested.

Respectfully submitted,

OBLON, SPIVAK, McCLELLAND,
MAIER & NEUSTADT, P.C.



Richard L. Treanor
Attorney of Record
Registration No.: 36,379



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Telephone: (703) 413-3000
Facsimile (703) 413-2220
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DOCKET NO.: 210136US99

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IN THE CLAIMS

Claims 1-20 (cancel)

Claims 21-31 (new)